

General Description

The Sanrise SRT04N016L is a low voltage power MOSFET, fabricated using advanced split gate trench technology. The resulting device has extremely low on resistance, low gate charge and fast switching time, making it especially suitable for applications which require superior power density and synchronous rectification.

The SRT04N016L break down voltage is 40V and it has a high rugged avalanche characteristics. The SRT04N016L is available in PDFN5*6 package.

Features

- Ultra Low $R_{DS(ON)_{TYP}} = 1.15m\Omega @ V_{GS} = 10V$.
- Ultra Low Gate Charge, $Q_g = 85nC$ typ.
- Fast switching capability
- Robust design with better EAS performance
- EMI Improved
- Non-automotive Qualified

Application

- Server/Telecom
- High Power Supply
- E-Tools
- BMS

Symbol

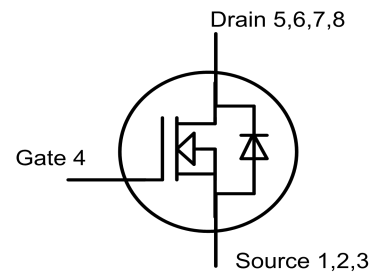
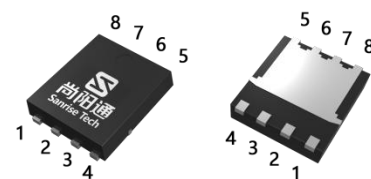


Figure 1 Symbol of SRT04N016L

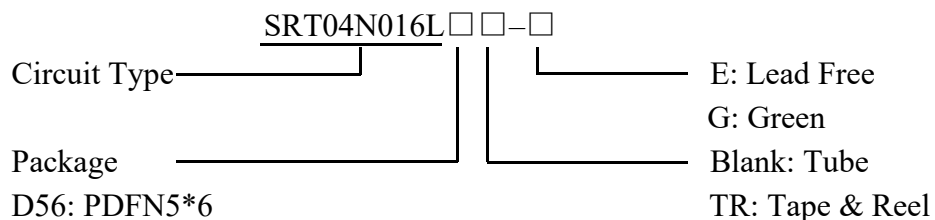
Package Type



PDFN5*6

Figure 2 Package Type of SRT04N016L

Ordering Information



Package	Part Number	Marking ID	Packing Type
PDFN5*6	SRT04N016LD56TR-G	SRT04N016LD56G	Tape & Reel

Absolute Maximum Ratings

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	40	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current, Silicon	$T_C=25^{\circ}C$	I_D	173	A
	$T_C=100^{\circ}C$		109	
	$T_C=125^{\circ}C$		77	
Pulsed Drain Current (Note 2)		I_{DM}	692	A
Avalanche Energy, Single Pulse (Note 3)		E_{AS}	100	mJ
Avalanche Destructive Energy, Single Pulse (Note 4)		E_{AS_Limit}	756	mJ
Avalanche Energy, Repetitive (Note 2)		E_{AR}	0.2	mJ
Avalanche Current, Repetitive (Note 2)		I_{AR}	50.0	A
Continuous Diode Forward Current		I_S	173	A
Diode Pulse Current		$I_{S,PULSE}$	692	A
Max Power Dissipation		P_D	100	W
Operating Junction Temperature		T_J	150	°C
Storage Temperature		T_{STG}	-55 to 150	°C
Lead Temperature (Soldering, 10 sec)		T_{LEAD}	260	°C

Note:

1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature
3. $I_{AS}=20A$, $V_{DD}=20V$, $R_G=25\Omega$, Starting $T_J=25^{\circ}C$
4. $I_{AS_Limit}=55A$, $V_{DD}=20V$, $R_G=25\Omega$, Starting $T_J=25^{\circ}C$

Thermal Resistance

Parameter		Symbol	Min	Typ	Max	Unit
Thermal Resistance, Junction-to-Case	PDFN5*6	R_{thJC}			1.2	°C/W
Thermal Resistance, Junction-to-Ambient	PDFN5*6	R_{thJA}			50	

Electrical Characteristics
 $T_J = 25^\circ\text{C}$, unless otherwise specified.

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Statistic Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	40			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=40V, V_{GS}=0V$			1	μA
Gate-Body Leakage Current	Forward	$I_{GSSF}, V_{GS}=20V, V_{DS}=0V$			200	nA
	Reverse	$I_{GSSR}, V_{GS}=-20V, V_{DS}=0V$			-200	
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}, I_D=0.25mA$	1.2	1.8	2.4	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=50A$		1.15	1.6	mΩ
		$V_{GS}=4.5V, I_D=50A$		2.0	3.05	
Gate Resistance	R_G	f=1MHz, Open Drain		1.3		Ω
Dynamic Characteristics						
Input Capacitance	C_{ISS}	$V_{DS}=20V, V_{GS}=0V, f=1MHz$		5.8		nF
Output Capacitance	C_{OSS}			1.6		nF
Reverse Transfer Capacitance	C_{RSS}			98		pF
Effective output capacitance, energy related ^{NOTE5}	$C_{O(er)}$	$V_{GS}=0V, V_{DS}=0\dots 32V$		2.4		nF
Effective output capacitance, time related ^{NOTE6}	$C_{O(tr)}$			3.0		
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=20V, I_D=50A, R_G=1.6\Omega, V_{GS}=10V$		18		ns
Rise Time	t_r			55		
Turn-off Delay Time	$t_{d(off)}$			60		
Fall Time	t_f			12		
Gate Charge Characteristics						
Gate to Source Charge	Q_{gs}	$V_{DD}=20V, I_D=50A, V_{GS}=0 \text{ to } 10V$		12.5		nC
Gate to Drain Charge	Q_{gd}			9.5		
Gate Charge Total	Q_g			85		
Gate Plateau Voltage	$V_{plateau}$			2.3		V
Gate Charge Total, sync FET	Q_g	$V_{DD}=0.1V, V_{GS}=0 \text{ to } 10V$		79		nC
Reverse Diode Characteristics						
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_{SD}=50A$		0.84	1.0	V
Reverse Recovery Time	t_{rr}	$V_R=20V, I_F=50A, dI_F/dt=100A/\mu s$		60		ns
Reverse Recovery Charge	Q_{rr}			120		nC
Peak Reverse Recovery Current	I_{rrm}			4.0		A

Note:

- $C_{O(er)}$ is a fixed capacitance that gives the same stored energy as C_{OSS} while V_{DS} is rising from 0 to 32V
- $C_{O(tr)}$ is a fixed capacitance that gives the same charging time as C_{OSS} while V_{DS} is rising from 0 to 32V



Sanrise Technology Limited Company

<http://www.sanrise-tech.com>

IMPORTANT NOTICE

Shenzhen Sanrise Technology Co., LTD. reserves the right to make changes without further notice to any products or specifications herein. Shenzhen Sanrise Technology Co., LTD. does not assume any responsibility for use of any its products for any particular purpose, nor does Shenzhen Sanrise Technology Co., LTD. assume any liability arising out of the application or use of any its products or circuits. Shenzhen Sanrise Technology Co., LTD. does not convey any license under its patent rights or other rights nor the rights of others.

Main Site:

- Headquarter

Shenzhen Sanrise Technology Co., LTD.
A1206, Skyworth building, No. 008, gaoxinnan 1st Road,
Gaoxin District, Yuehai street,, Nanshan District, ShenZhen,
P.R.China
Tel: +86-755-22953335
Fax: +86-755-22916878

- Shanghai Office

Sanrise Technology Limited Company
Rm.401, Building B, No. 666, Zhangheng Road,
Zhangjiang Hi-Tech Park, Shanghai, P.R.China
Tel: +86-21-68825918